Supplemental Information

5 nm Thick Indium Nitride Channel Layers Fabricated by PEALD for 3D Transistor Architectures

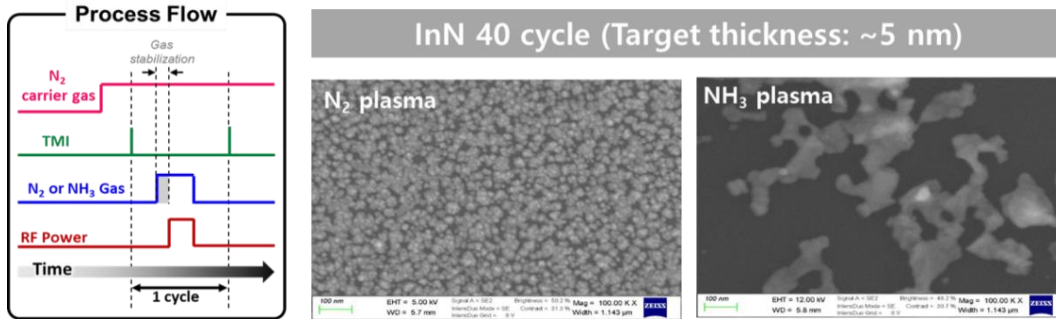

Fig. 1. Process flow of InN ALD using TMI and N_2 or NH_3 plasma (left). InN film conformality after 40 cycle process (right).

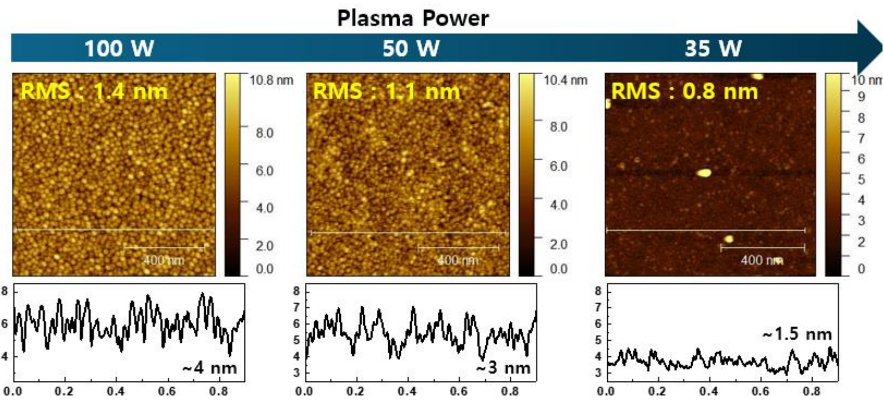

Fig. 2. Roughness changes of InN thin film according to N_2 plasma power

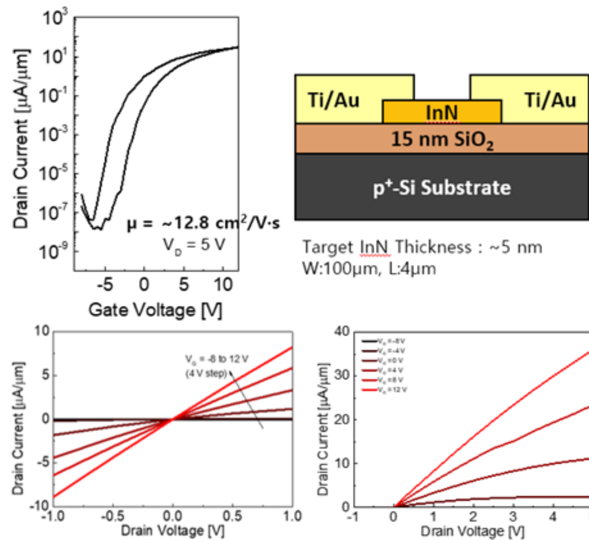

Fig. 3. Transfer and output curves of 5 nm InN devices (V_D = 5 V, W = 100 μm, L = 4 μm).